

ABSTRACT OF THE DISCLOSURE

A ball-up preventive layer is formed on a first substrate. A bonding layer made of eutectic material is formed on the ball-up preventive layer. A semiconductor light emitting structure is formed on a second substrate. A first 5 electrode is formed at least partially on the semiconductor light emitting structure. A barrier layer is formed on the first electrode. A metal layer is formed on the barrier layer. The bonding layer and the metal layer are bonded together. The second substrate is removed from the bonded structure. A second electrode is formed on a partial surface area of the semiconductor light emitting structure 10 exposed on a surface of the bonded structure to obtain a semiconductor light emitting device.